

ABSTRACT OF THE DISCLOSURE

A semiconductor layer in which a primary part of a FinFET is formed, i.e., a fin has a shape which is long in a direction x and short in a direction y .

5 A width of the fin in the direction y changes on three stages. First, in a channel area between gate electrodes each having a gate length L_g , the width of the fin in the direction y is W_{ch} . Further, the width of the fin in the direction y in a source/drain extension area adjacent to the channel area in the
10 direction x is W_{ext} ($> W_{ch}$). Furthermore, the width of the fin in the direction y in a source/drain area adjacent to the source/drain extension area in the direction x is W_{sd} ($> W_{ext}$).